

## **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from Process 03.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CES</sub>	Collector-Emitter Voltage	80	V	
V <sub>CBO</sub>	Collector-Base Voltage	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	12	V	
I <sub>C</sub>	Collector Current - Continuous	800	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах			Units
		MPSA28	*MMBTA28	**PZTA28	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

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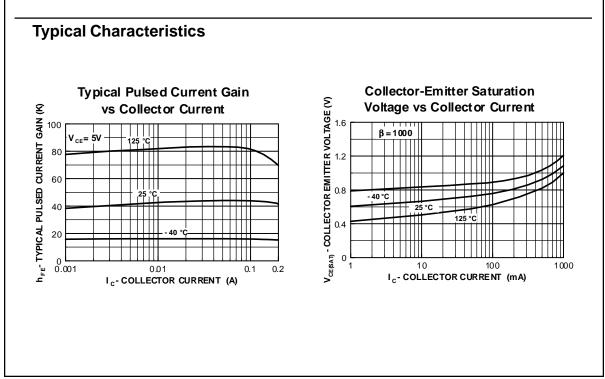
(continued)

Electri	Electrical Characteristics TA=25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Мах	Units	
OFF CHAI	RACTERISTICS					
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	80		V	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	80		V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	12		V	
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 60 \text{ V}, I_E = 0$		100	nA	
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = 60 \text{ V}, \text{ V}_{BE} = 0$		500	nA	
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		100	nA	
ON CHAR	ACTERISTICS				-	
h <sub>FE</sub>	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 10,000			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.01$ mA $I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA		1.2 1.5	V	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 5.0 V		2.0	V	

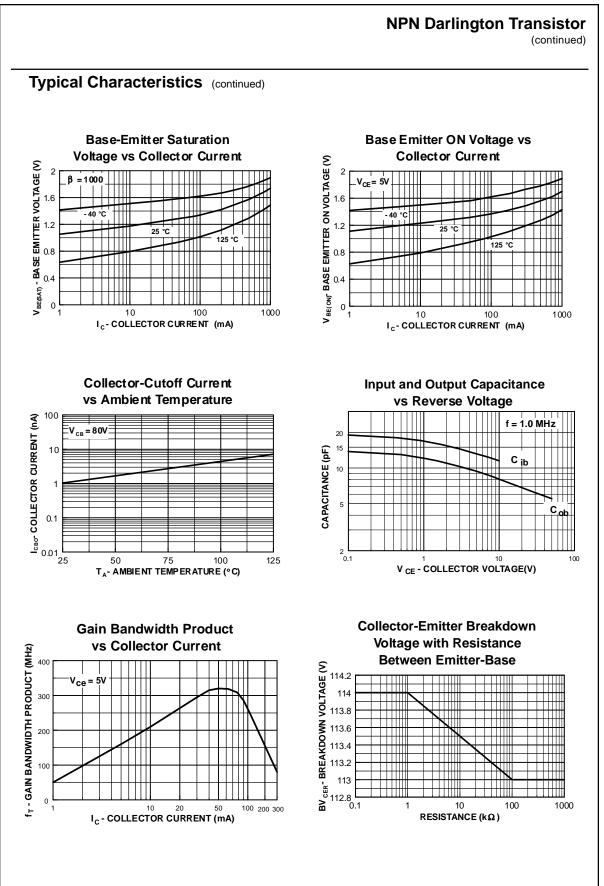
## SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	125		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 1.0 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		8.0	pF

\*Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%



MPSA28/MMBTA28/PZTA28, Rev A



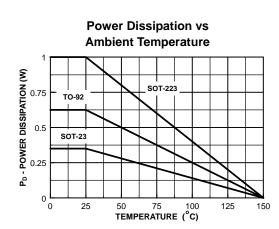
MPSA28/MMBTA28/PZTA28, Rev A

# MPSA28 / MMBTA28 / PZTA28

# NPN Darlington Transistor







MPSA28/MMBTA28/PZTA28, Rev A



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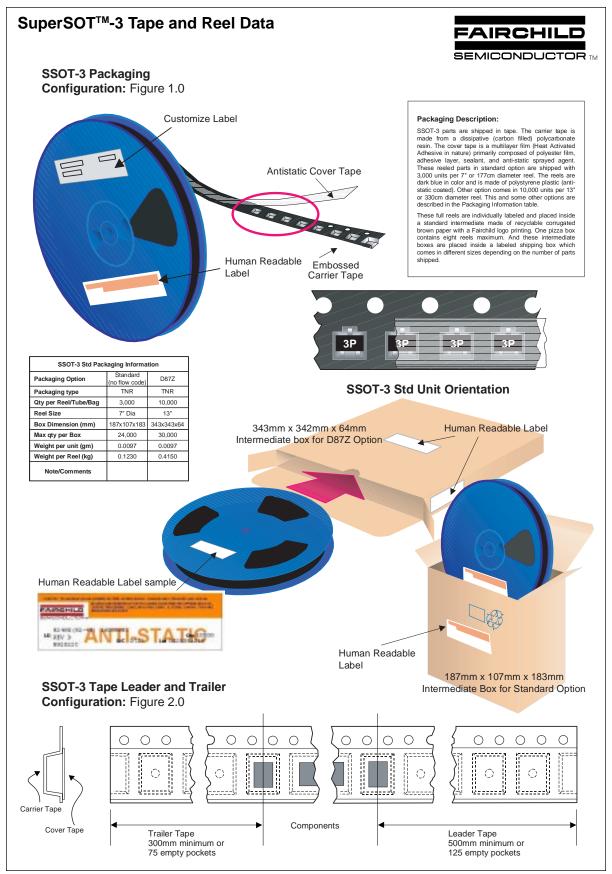
March 2001, Rev. B1





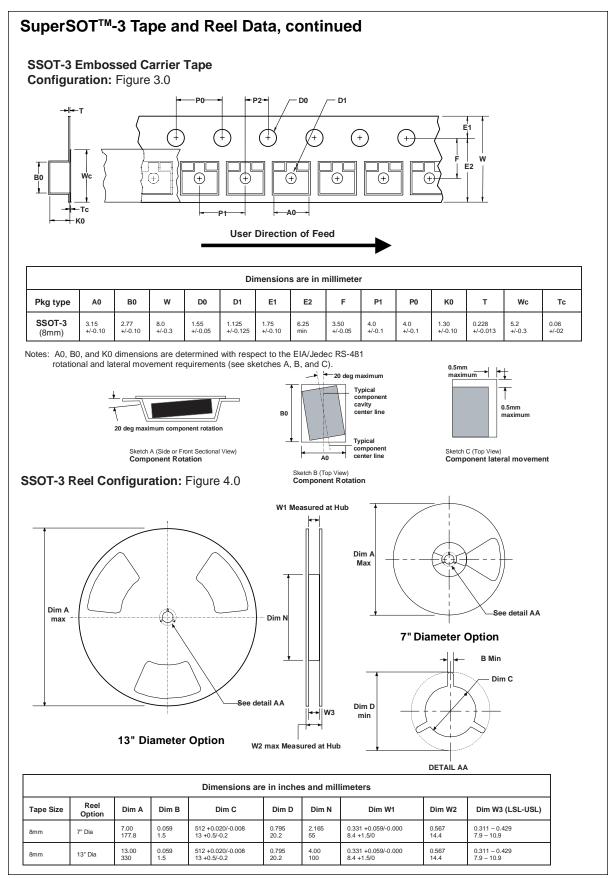
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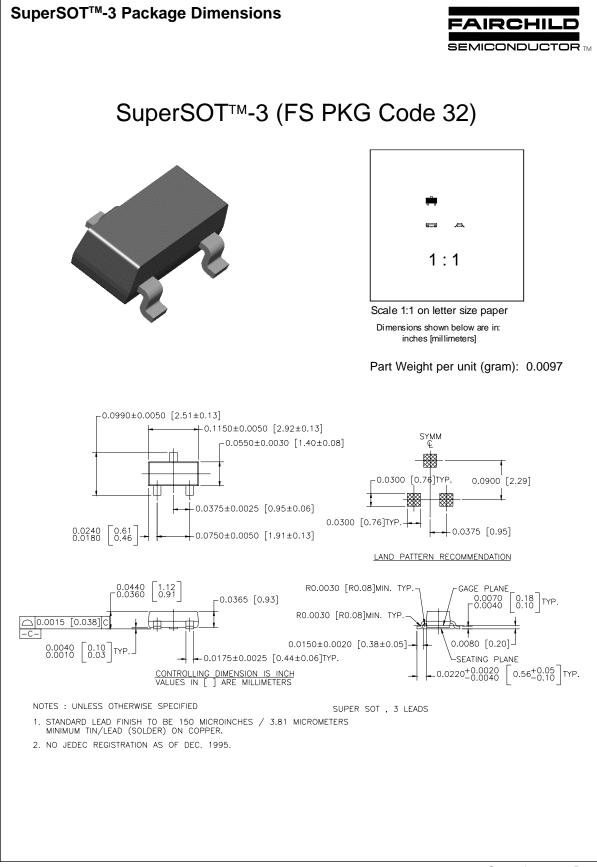


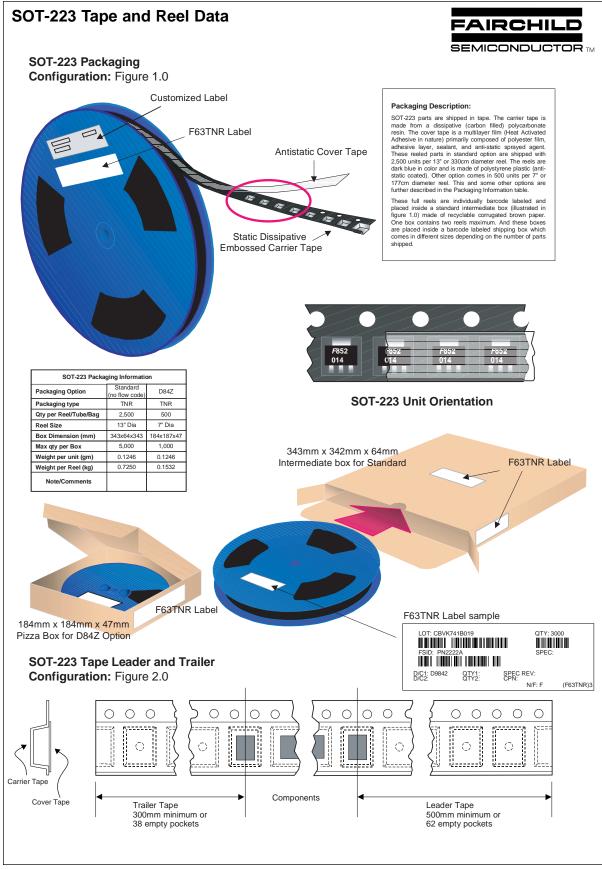
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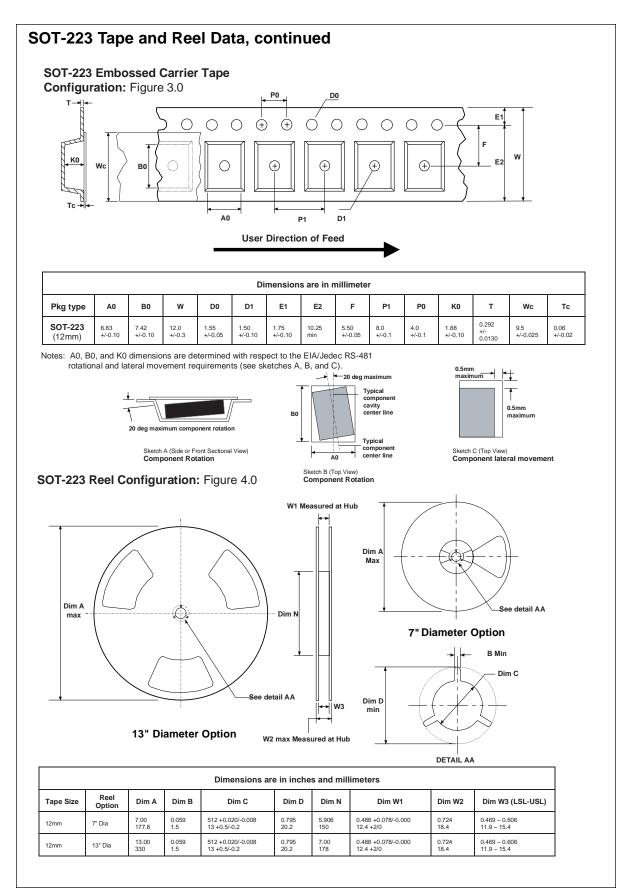
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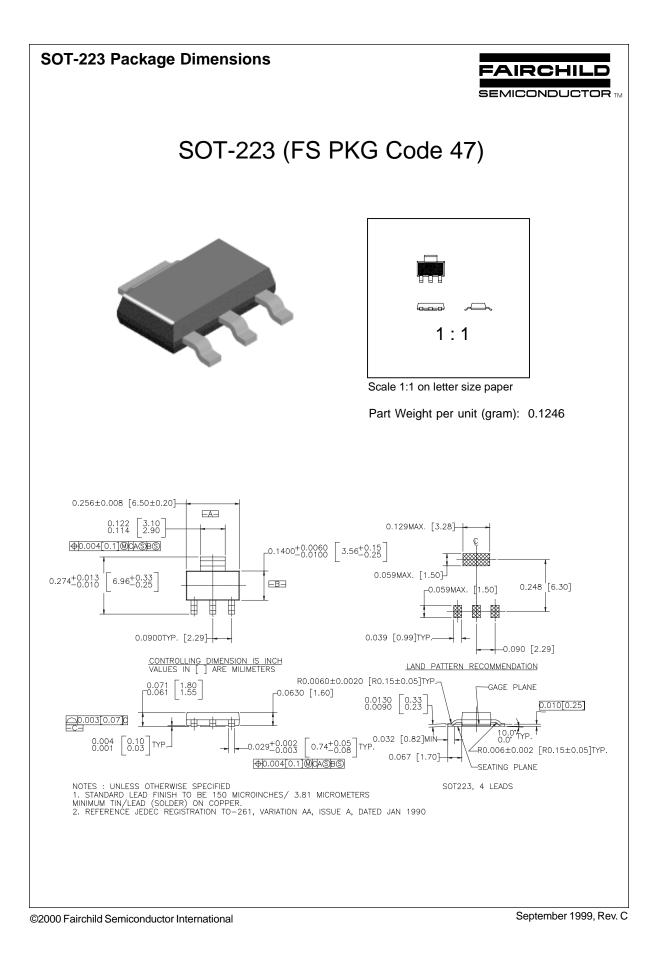




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